

IN THE CLAIMS:

Please cancel claims 1 and 2. Please also rewrite claims 3, 5, and 20 to read as follows (it being noted that an Attachment to this Amendment is marked-up to show the changes from the previous version of these claims):

3. (Twice Amended) A semiconductor integrated circuit device, comprising:

a source region formed on a semiconductor substrate;

a first conductor having a first resistivity formed over said source region;

a first contact group having contacts connecting said source region and said first conductor;

a second conductor having a second resistivity over said first conductor;

a second contact group having contacts connecting said first conductor and said second conductor;

a drain region formed on said semiconductor substrate;

a third conductor having said first resistivity formed over said drain region;

a third contact group having contacts connecting said drain region and said third conductor;

a fourth conductor having said second resistivity formed over said third conductor;

a fourth contact group having contacts connecting said third conductor and said fourth conductor;

wherein a total number of contacts in said first contact group is different from a total number of contacts in said second contact group, and

B1
a total number of contacts in said third contact group is different from a total number of contacts in said fourth contact group.

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B2
(Twice Amended) The semiconductor integrated circuit device as claimed in claim 1, wherein said first resistivity is higher than said second resistivity, and a total number of contacts in said first contact group and in said third contact group is greater than a total number of contacts in said second contact group and in said fourth contact group.

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B3
(Amended) A transistor according to claim 16, wherein a distance from an end of the source region to a nearest one of the first contacts is equal to or greater than a distance from the gate electrode to said nearest one of the first contacts.
